

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Garbuzov et al. Art Unit : Unknown  
Serial No. : Examiner : Unknown  
Filed : February 13, 2004  
Title : HIGH POWER SEMICONDUCTOR LASER DIODE

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Applicant submits the references listed on the attached form PTO-1449 identified as Desig. ID "AB", "AC", "AD", "AE", "AF", "AG", "AH", and "AI".

Under 35 USC §120, this application relies on the earlier filing date of application serial number 08/757,883, filed on November 27, 1996. The references that were not identified in the previous paragraph were submitted to and/or cited by the Office in the prior application and, therefore, are not provided in this application.

This statement is being filed with the application. Accordingly, only copies of foreign patent documents and non-patent literature are enclosed. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 2/13/04

  
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Substitute Form PTO-1449 (Modified)		U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. <b>14564-006002</b>	Application No.
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))		Applicant		
		Filing Date	Group Art Unit	

<b>U.S. Patent Documents</b>							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	5,661,742	Aug. 26, 1997	Huang et al.			

<b>Other Documents (include Author, Title, Date, and Place of Publication)</b>		
Examiner Initial	Desig. ID	Document
	AB	Ablyazov et al. "Possibility of increasing the maximum radiation intensity in heterolasers with a wide waveguide," Sov. J. Quantum Electron, vol. 20, no. 1, pp. 1320-1323 (1990).
	AC	Cockerill et al. "Depressed index cladding graded barrier separate confinement single quantum well heterostructure laser," Appl. Phys. Lett., vol. 59, no. 21, pp. 2694-2607 (1991).
	AD	Emanuel et al., "High-Efficiency AlGaAs-Based Laser Diode at 808 nm with Large Transverse Spot size," IEEE Photonics Technology Letters, vol. 8, no. 10, pp. 1291-1293, (1996).
	AE	Garbuzov et al., " High-Power 0.8 μm InGaAsP-GaAs SCH SQW Lasers," IEEE Journal of Quantum Electronics, vol. 27, no. 6, pp. 1531-1536 (1991).
	AF	Garbuzov et al., "High Power separate confinement heterostructure AlGaAs/GaAs laser diodes with broadened waveguide," SPIE, vol. 2692, pp. 20-28, (1996).
	AG	Mawst et al., "8 W continuous wave front-facet power from broad-waveguide Al-free 980 nm diode lasers," Appl. Phys. Lett., vol. 69, no. 11, pp. 1532-1534 (1996).
	AH	Petrescu-Prahova, "High Power low confinement AlGaAs/GaAs single quantum well laser diode operating in the fundamental lateral mode," Conference Proceedings, Conference on Lasers 7 Electro-Optics (CLEO) Tuesday Afternoon / Europe, page 171 (1994).
	AI	Waters, et al., "Dark-Line-Resistant Diode Laser at 0.8 μm Comprising InAlGaAs Strained Quantum Well," IEEE Photonics Technology Letters, vol. 3, no. 5, pp. 409-411 (1991).

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	